Part Number	Customer

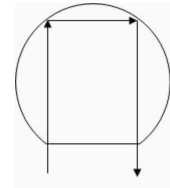
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	NONE	
	5.0	Overall Thickness	380.50 +/- 10.50 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ESTIMATE. ADE to ASTM F534, 20%
	8.0	Warp	<80.00µm	ESTIMATE. ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Edge Rounding	Semi Standard Edge Rounding.	Guaranteed by process
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	350.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	0.01 - 0.02 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide and laser mark SEMI M-13, "U41-nnn to U41-nnn" where nnn in 001-100, non-consecutive numbers acceptable	Wafer Vendor
	19.0	Backside Oxide thickness	2,500.00 +/- 250.00 A	Guaratneed by process, thickness ref. Front Field Oxide
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	5,000.00 +/- 250.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle Wafer	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	25.0	Nominal Thickness	30.00 +/- 0.50 µm	30um +/- 0.3um BEST EFFORT. FTIR, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	27.0	Device Doping Type	P	Wafer Vendor
	28.0	Device Dopant	Boron	Wafer Vendor
	29.0	Device Resistivity	0.01 - 0.02 Ohmcm	Wafer Vendor
	30.0	Device Field Oxidation	2,500.00 +/- 250.00 A	Nanospec centre point, 4%

Part Number	Customer

Category		Parameter	Specification	Measurement Method
DeviceSilicon	31.0	Dislocation Etch Pit Density	<100 / cm2	Wafer vendor
	32.0	Oxygen Concentration	<15 ppma (ASTM F121-83)	Wafer vendor
	33.0	Voids	none	Bright Light, 100% (note 2)
	34.0	Scratches	0	Bright Light, 100% (note 2)
	35.0	Haze	none	Bright Light, 100% (note 2)

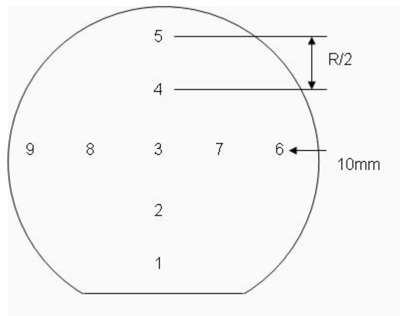
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information